

The Comparison of Lithium Doping Impact to Solution Processed  
ZnO/InZnO Thin Film Transistors' Characteristics

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Abstract

We report the impact of lithium doping to ZnO/InZnO thin film transistors' electrical and optical characteristics. A best device with mobility  $\square 0.94$  cm<sup>2</sup>/vs, and an on/off current ratio over 10<sup>6</sup> were achieved. Further, the high ionization energy of lithium (5.39eV) led the transistor stabilizer than which without lithium doping.

Key words : InZnO; Transistor; ZnO